





N-CHANNEL ENHANCEMENT MODE MOSFET

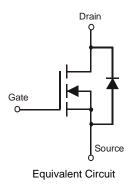
Features

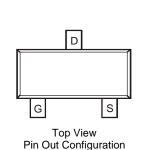
- Low On-Resistance: R_{DS(ON)}
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Notes 3 & 4)
- ESD Protected Up To 2kV

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)







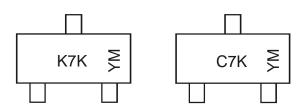
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN601K-7	SOT23	3000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.
- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com
- 3. Product manufactured with Date Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K = SAT (Shanghai Assembly / Test site)
C = CAT (Chengdu Assembly / Test site)
7K = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: S = 2005)
M = Month (ex: 9 = September)

Date Code Key

Year	2005	2006	2007	2008	2009	2010	2011	2011	2012	2013	2014	2015	2016	2017
Code	S	T	U	V	W	Х	Υ	Υ	Z	Α	В	С	D	Е
Month	Jan	Feb	Ма	ır /	Apr	May	Jun	Jul	Aug	Se	р (Oct	Nov	Dec
Code	1	2	3		4	5	6	7	8	9		0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Prain Current (Note 5)	Continuous	1-	300	m ^
Drain Current (Note 5)	Pulsed (Note 6)	ID	800	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

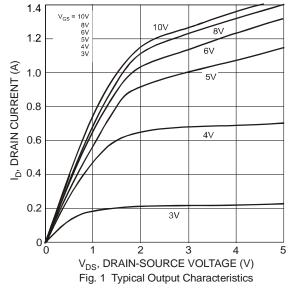
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	350	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	357	°C/W
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-65 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					•	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)	-			a.		
Gate Threshold Voltage	V _{GS(th)}	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$
Static Drain-Source On-Resistance	٥	_		2.0	1 ()	$V_{GS} = 10V, I_D = 0.5A$
Static Dialit-Source Off-Resistance	R _{DS (ON)}	_		3.0		$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS		_	_	_	-	
Input Capacitance	C _{iss}	_	_	50	pF	
Output Capacitance	Coss			25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}		_	5.0	pF	

- 5. Device mounted on FR-4 PCB.
- 6. Pulse width ≤10μS, Duty Cycle ≤1%.
 7. Short duration pulse test used to minimize self-heating effect.





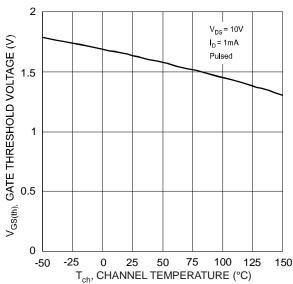


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

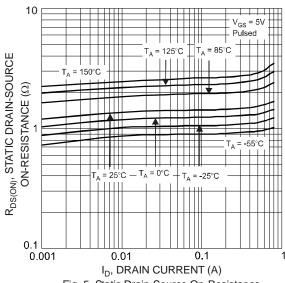
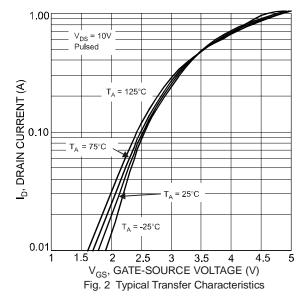


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



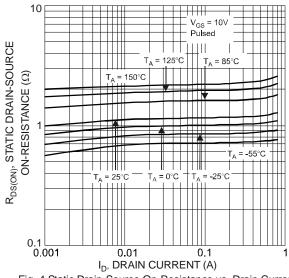


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

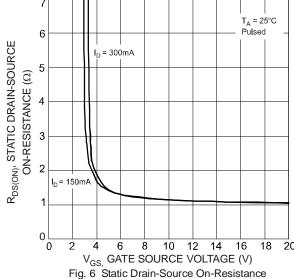
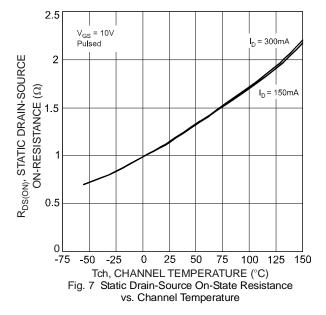
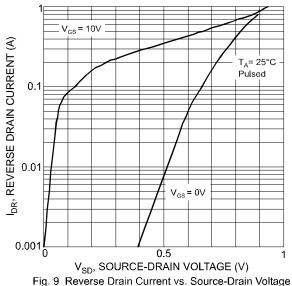
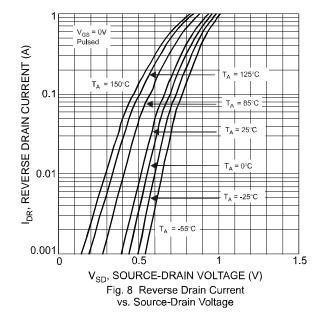


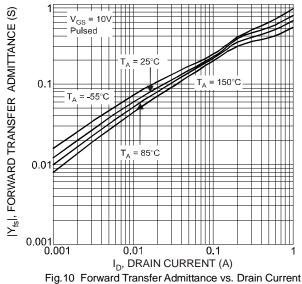
Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



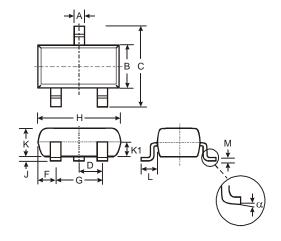








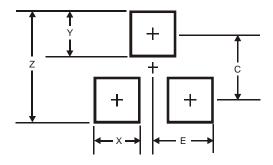
Package Outline Dimensions



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
C	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Η	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All	All Dimensions in mm							



Suggested Pad Layout



Dimensions	Value (in mm)				
Z	2.9				
Х	0.8				
Y	0.9				
С	2.0				
E	1.35				

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